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- S50: (3) S89 and depant
- S51: (3) Backward citation search 3
- S52: (3) Forward citation search 6
- S53: (486) substrate and "GaN" and (active adj /layer or  
S54: (12) (US-20020006726-S or US-20040375037-S).did. or  
S55: (483) S83 not (goett-werner-k.in. camras-michael-d  
S56: (476) S55 not S84
- S57: (416) S86 and (light adj emitt&) S58: (285) S87 and (concentration with (var&S or chang&  
S59: (33) S88 and (n-type with ((compound or composition  
S60: (85) S89 and (p-type with ((compound or composition  
S61: (82) S80 and (electrode or contact)
- S62: (9) S61 and nitride and thickness

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T-Score  
of Nitride Semiconductors

S61 and nitride and thickness

U	S	P	E	Document ID	Source	Issue Date	Pages	Title	Current OR	C-
	r	r	r	US 6337893 B1	USPAT	20020108	19	Nitride semiconductor device	257/79	2
	r	r	r	US 6320307 B1	USPAT	20011120	11	Light emitting device having flat growth GaN layer	257/101	2
	r	w	r	US 6215133 B1	USPAT	20010410	18	Light-emitting gallium nitride-based compound semiconductor device	257/96	2
	r	w	r	US 6204084 B1	USPAT	20010320	38	Nitride system semiconductor device and method for manufacturing the same	438/46	2
	r	w	r	US 6147364 A	USPAT	20001114	31	Compound semiconductor device formed of nitrogen-containing gallium compound such as GaN, AlGaN or InGaN	257/76	2
	r	w	r	US 5993017 A	USPAT	19990611	31	Compound semiconductor device formed of nitrogen-containing gallium compound such as GaN, AlGaN or InGaN	257/196	2
	r	w	r	US 5829486 A	USPAT	19990309	17	Light-emitting gallium nitride-based compound semiconductor device	257/96	2
	r	w	r	US 5740192 A	USPAT	19980414	34	Semiconductor laser	372/48	2
	r	r	r	US 6613009 B2	USPAT	20050208	20	Light-emitting semiconductor device using gallium nitride compound semiconductor	257/94	2
10	r	r	r	US 6238633 B2	USPAT	20050104	38	Nitride semiconductor device	257/14	2
11	r	c	r	US 6216465 B2	USPAT	20041116	41	Nitride semiconductor element and production method for nitride semiconductor element	438/22	2
12	r	r	r	US 6815728 B2	USPAT	20041109	18	Nitride semiconductor light-emitting device and optical device and light-emitting apparatus with the nitride semiconductor light-emitting dev	257/93	2
13	r	r	r	US 6737330	USPAT	20030928	13	Boron phosphide-based semiconductor device and production method thereof	257/102	2

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